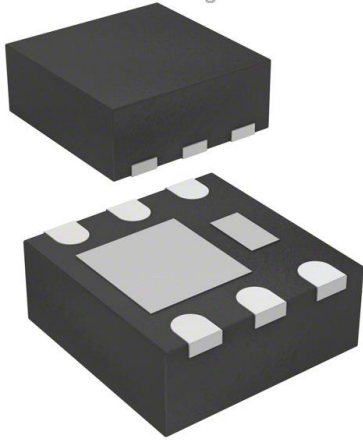


FDMA86551L Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FDMA86551L-DG
Manufacturer	onsemi
Manufacturer Product Number	FDMA86551L
Description	MOSFET N-CH 60V 7.5A 6MICROFET
Detailed Description	N-Channel 60 V 7.5A (Ta) 2.4W (Ta) Surface Mount 6-MicroFET (2x2)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

FDMA86551L

Series:

PowerTrench®

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

3V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

6-MicroFET (2x2)

Base Product Number:

FDMA86551

Manufacturer:

onsemi

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

7.5A (Ta)

Rds On (Max) @ Id, Vgs:

23mOhm @ 7.5A, 10V

Gate Charge (Qg) (Max) @ Vgs:

17 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

1235 pF @ 30 V

Power Dissipation (Max):

2.4W (Ta)

Mounting Type:

Surface Mount

Package / Case:

6-WDFN Exposed Pad

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET – Single N-Channel, POWERTRENCH®

60 V, 7.5 A, 23 mΩ

FDMA86551L

General Description

This device has been designed to provide maximum efficiency and thermal performance for synchronous buck converters. The low $R_{DS(on)}$ and gate charge provide excellent switching performance.

Features

- Max $R_{DS(on)}$ = 23 mΩ @ $V_{GS} = 10$ V, $I_D = 7.5$ A
- Max $R_{DS(on)}$ = 35 mΩ @ $V_{GS} = 4.5$ V, $I_D = 6$ A
- Low Profile – 0.8 mm Maximum in the New Package
MicroFET™ 2x2 mm
- This Device is Pb-Free, Halide Free and RoHS Compliant

Applications

- DC-DC Buck Converters

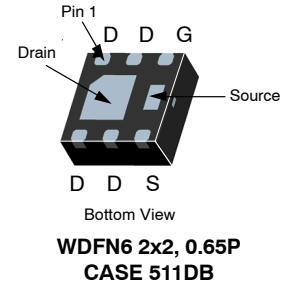
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	60	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		A
	– Continuous (Note 1a) $T_A = 25^\circ\text{C}$	7.5	
	– Pulsed (Note 4)	45	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	37	mJ
P_D	Power Dissipation (Note 1a) $T_A = 25^\circ\text{C}$	2.4	W
	Power Dissipation (Note 1b) $T_A = 25^\circ\text{C}$	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

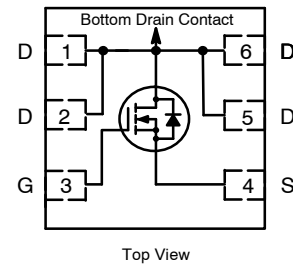
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

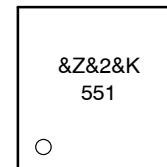
Symbol	Parameter	Rated	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	



PIN CONNECTIONS

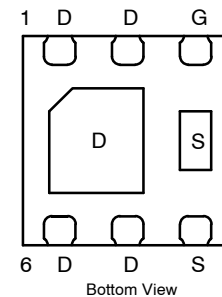


MARKING DIAGRAM



- &Z = Assembly Plant Code
- &2 = Data Code (Year & Week)
- &K = Lot Run Code
- 551 = Specific Device Code

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDMA86551L

ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	60	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	–	31	–	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48\ \text{V}$, $V_{GS} = 0\ \text{V}$	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}$, $V_{DS} = 0\ \text{V}$	–	–	100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	1.0	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	–	–5	–	mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$, $I_D = 7.5\ \text{A}$	–	19	23	m Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 6\ \text{A}$	–	26	35	
		$V_{GS} = 10\ \text{V}$, $I_D = 7.5\ \text{A}$, $T_J = 125^\circ\text{C}$	–	28	33	
g_{FS}	Forward Transconductance	$V_{DD} = 5\ \text{V}$, $I_D = 7.5\ \text{A}$	–	21	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1.0\ \text{MHz}$	–	881	1235	pF
C_{oss}	Output Capacitance		–	182	255	
C_{rss}	Reverse Transfer Capacitance		–	6.1	15	
R_G	Gate Resistance		0.1	0.5	1.5	

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\ \text{V}$, $I_D = 7.5\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_{GEN} = 6\ \Omega$	–	7.3	15	ns
t_r	Rise Time		–	1.7	10	
$t_{d(off)}$	Turn-Off Delay Time		–	16	29	
t_f	Fall Time		–	1.4	10	
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $10\ \text{V}$, $V_{DD} = 30\ \text{V}$, $I_D = 7.5\ \text{A}$	–	12	17	nC
		$V_{GS} = 0\ \text{V}$ to $4.5\ \text{V}$, $V_{DD} = 30\ \text{V}$, $I_D = 7.5\ \text{A}$	–	5.8	8.1	
Q_{gs}	Gate to Source Charge	$V_{DD} = 30\ \text{V}$, $I_D = 7.5\ \text{A}$	–	2.7	3.8	
Q_{gd}	Gate to Drain "Miller" Charge		–	1.4	2.0	

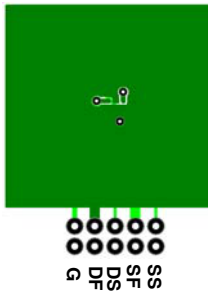
DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}$, $I_S = 2\ \text{A}$ (Note 2)	–	0.8	1.2	V
		$V_{GS} = 0\ \text{V}$, $I_S = 7.5\ \text{A}$ (Note 2)	–	0.9	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 7.5\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$	–	23	37	ns
Q_{rr}	Reverse Recovery Charge		–	9.7	19	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a. $52^\circ\text{C}/\text{W}$ when mounted
on a 1 in² pad of 2 oz copper



b. $145^\circ\text{C}/\text{W}$ when mounted
on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%
- E_{AS} of 37 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\ \text{mH}$, $I_{AS} = 5\ \text{A}$, $V_{DD} = 60\ \text{V}$, $V_{GS} = 10\ \text{V}$. 100% test at $L = 0.1\ \text{mH}$, $I_{AS} = 16\ \text{A}$.
- Pulsed I_D measured at $t_d \leq 250\ \mu\text{s}$, refer to Figure 11 SOA graph for more details.

FDMA86551L

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

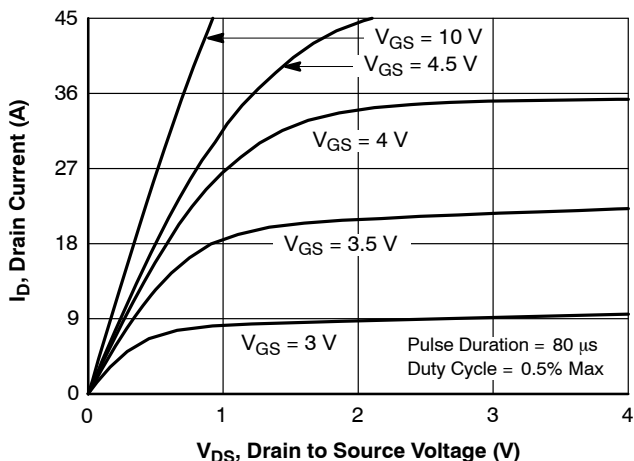


Figure 1. On-Region Characteristics

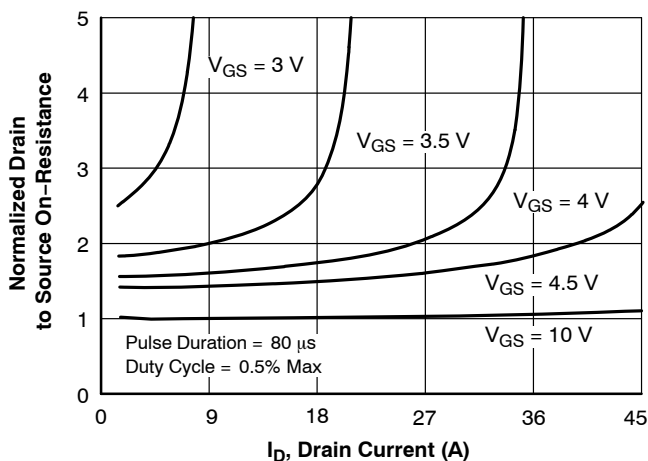


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

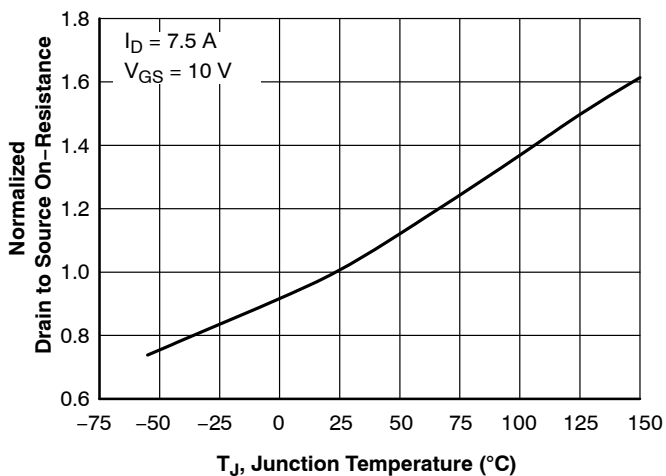


Figure 3. Normalized On-Resistance vs. Junction Temperature

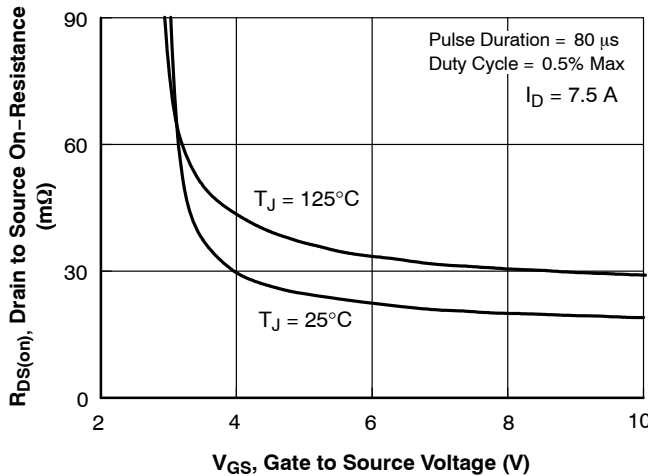


Figure 4. On-Resistance vs. Gate to Source Voltage

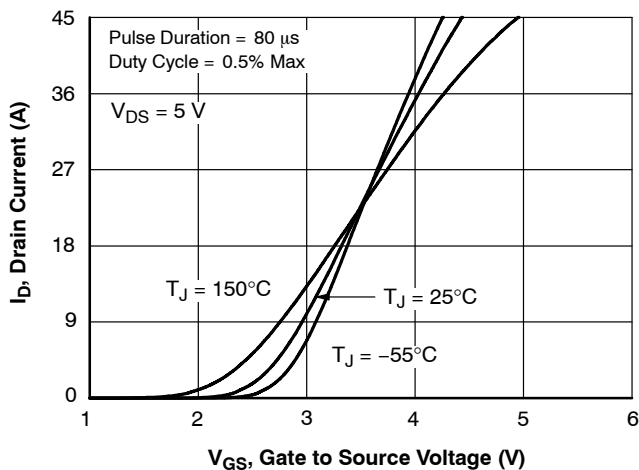


Figure 5. Transfer Characteristics

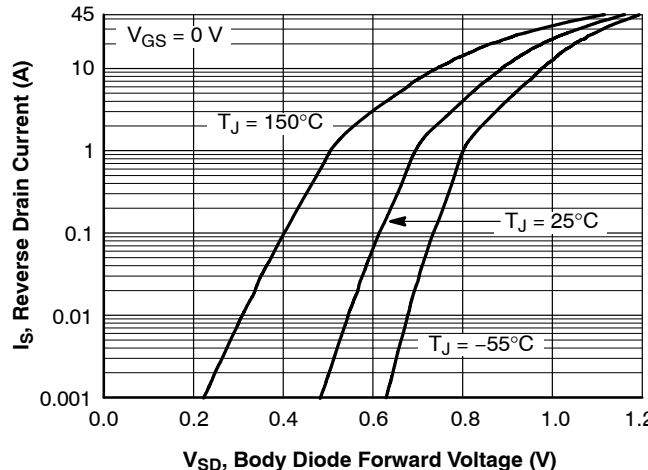


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

FDMA86551L

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

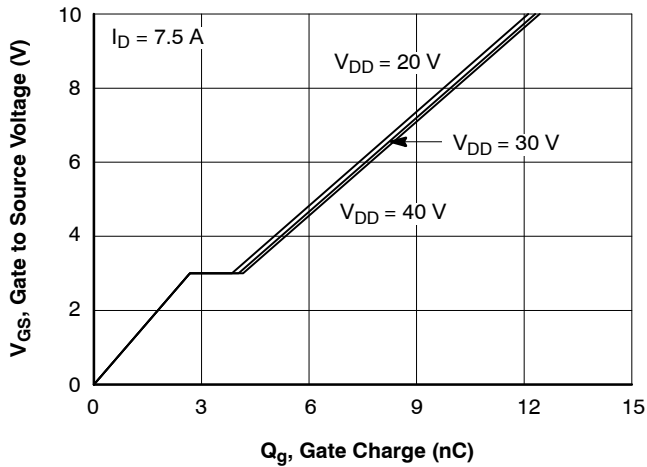


Figure 7. Gate Charge Characteristics

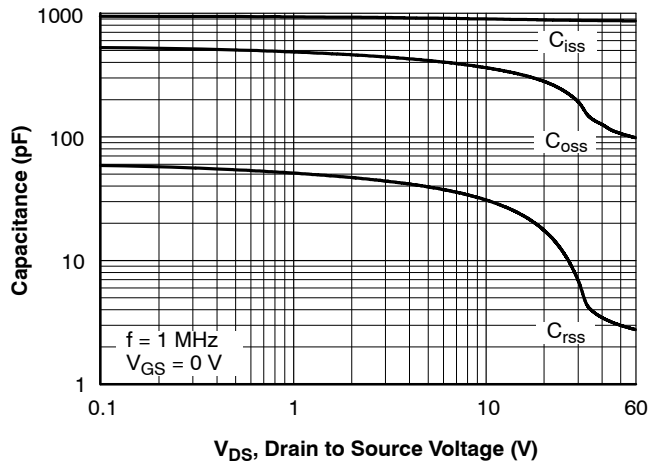


Figure 8. Capacitance vs. Drain to Source Voltage

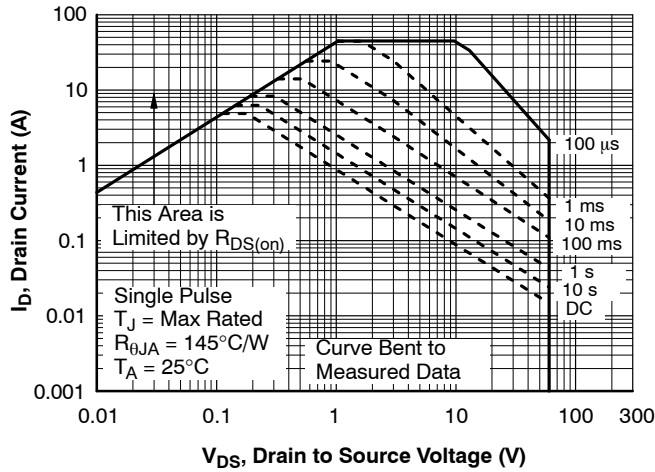


Figure 9. Forward Bias Safe Operating Area

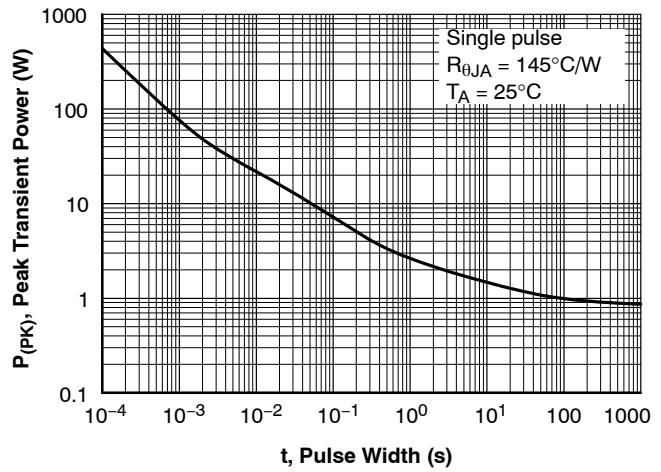


Figure 10. Single Pulse Maximum Power Dissipation

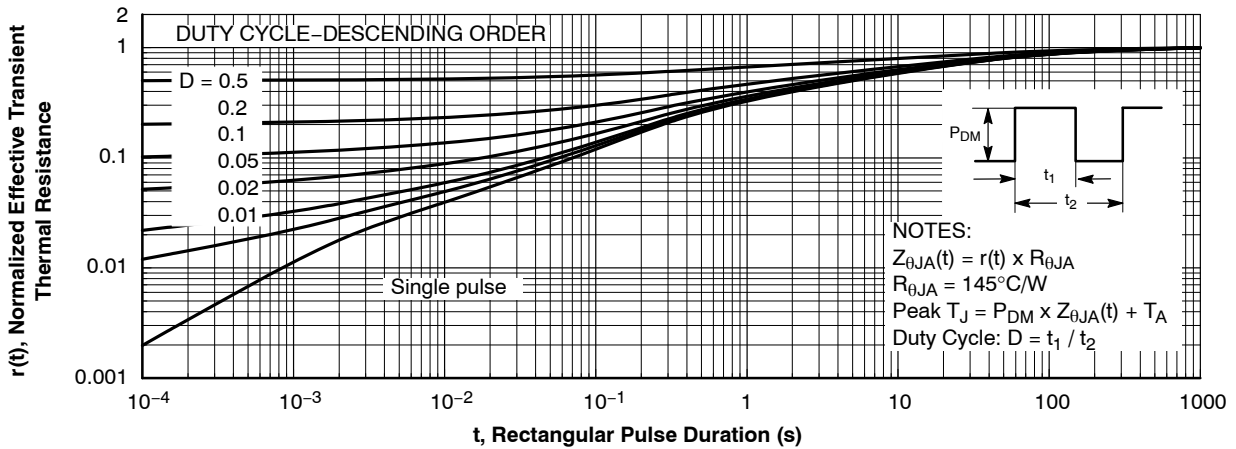


Figure 11. Junction-to-Ambient Transient Thermal Response Curve

FDMA86551L**ORDERING INFORMATION**

Device	Device Marking	Package Type	Reel Size	Tape Width	Shipping [†]
FDMA86551L	551	WDFN6 2x2, 0.65P (Pb-Free/Halide Free)	7"	8 mm	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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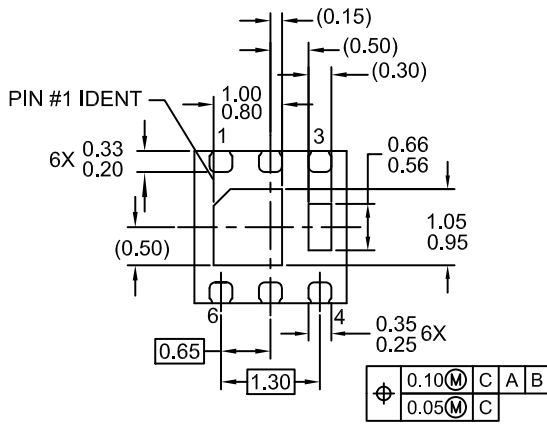
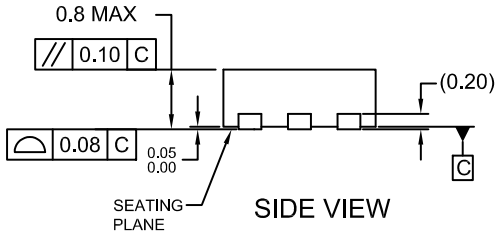
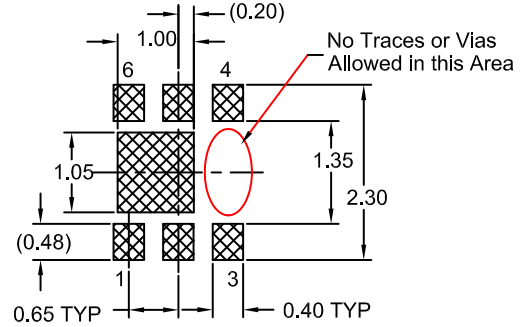
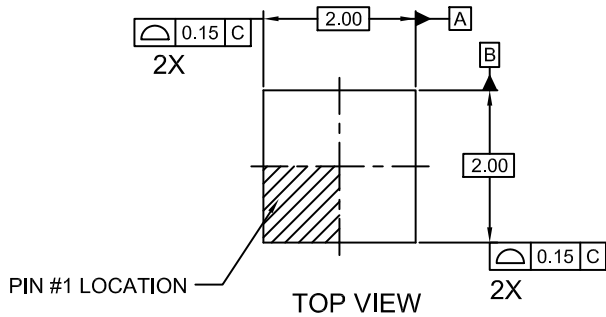
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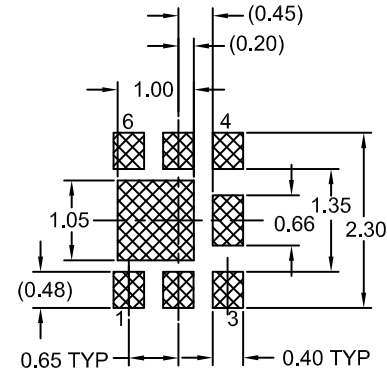
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**

WDFN6 2x2, 0.65P
CASE 511DB
ISSUE O

DATE 31 AUG 2016



RECOMMENDED LAND PATTERN OPT 1



NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

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